

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

2SC3329

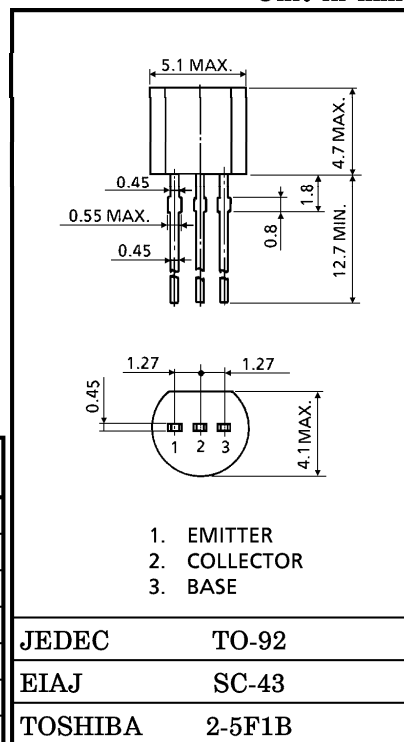
FOR LOW NOISE AUDIO AMPLIFIER APPLICATIONS AND
RECOMMENDED FOR THE FIRST STAGES OF MC HEAD AMPLIFIERS

Unit in mm

- Very Low Noise in the Region of Low Signal Source Impedance
Equivalent Input Noise Voltage : $E_n = 0.6nV/\sqrt{Hz}$ (Typ.)
- Low Pulse Noise. Low 1/f Noise
- Low Base Spreading Resistance : $r_{bb'} = 2.0 \Omega$ (Typ.)
- Complementary to 2SA1316

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CBO}	80	V
Collector-Emitter Voltage	V _{CEO}	80	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	I _C	100	mA
Base Current	I _B	20	mA
Collector Power Dissipation	P _C	400	mW
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _{stg}	-55~125	°C



Weight : 0.21 g

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 80\text{ V}, I_E = 0$	—	—	0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 5\text{ V}, I_C = 0$	—	—	0.1	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1\text{ mA}, I_B = 0$	80	—	—	V
DC Current Gain	h_{FE} (Note)	$V_{CE} = 6\text{ V}, I_C = 2\text{ mA}$	200	—	700	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10\text{ mA}, I_B = 1\text{ mA}$	—	—	0.1	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = 6\text{ V}, I_C = 2\text{ mA}$	—	0.6	—	V
Base Spreading Resistance	$r_{bb'}$	$V_{CE} = 6\text{ V}, I_C = 1\text{ mA},$ $f = 100\text{ MHz}$	—	2.0	—	Ω
Transition Frequency	f_T	$V_{CE} = 6\text{ V}, I_C = 1\text{ mA}$	—	42	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	6.2	—	pF
Noise Figure	NF	$V_{CE} = 6\text{ V}, I_C = 0.1\text{ mA}$ $f = 10\text{ Hz}, R_G = 10\text{ k}\Omega$	—	2	6	dB
		$V_{CE} = 6\text{ V}, I_C = 0.1\text{ mA}$ $f = 1\text{ kHz}, R_G = 10\text{ k}\Omega$	—	1	2	
		$V_{CE} = 6\text{ V}, I_C = 0.1\text{ mA}$ $f = 1\text{ kHz}, R_G = 100\ \Omega$	—	2.5	—	

Note : h_{FE} Classification GR : 200~400, BL : 350~700

